

# **VP2450N3-G Information**



For Reference Only

Part Number VP2450N3-G

Manufacturer Microchip Technology

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH 500V 0.1A TO92-3 **Package** TO-226-3, TO-92-3 (TO-226AA)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **VP2450N3-G Specifications**

Manufacturer Part Number         VP2450N3-G           Manufacturer         Microchip Technology           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-226-3, TO-92-3 (TO-226AA)           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         100mA (Tj)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         3.5V @ ImA           Gate Charge (Qg) (Max) @ Vgs         190pF @ 25V           Vgs (Max)         ± 20V           FET Feature         -           Power Dissipation (Max)         740mW (Ta)           Rds On (Max) @ Id, Vgs         30 Ohm @ 100mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-92-3           Package / Case         TO-226-3, TO-92-3 (TO-226AA)		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-226-3, TO-92-3 (TO-226AA)           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         100mA (Tj)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         3.5V @ ImA           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         190pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         740mW (Ta)           Rds On (Max) @ Id, Vgs         30 Ohm @ 100mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-92-3           Package / Case         TO-226-3, TO-92-3 (TO-226AA)	Manufacturer Part Number	VP2450N3-G
Package         To-226-3, To-92-3 (To-226AA)           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         100mA (Tj)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         3.5V @ ImA           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         190pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         740mW (Ta)           Rds On (Max) @ Id, Vgs         30 0hm @ 100mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-92-3           Package / Case         TO-226-3, TO-92-3 (TO-226AA)	Manufacturer	Microchip Technology
Package         TO-226-3, TO-92-3 (TO-226AA)           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         100mA (Tj)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         3.5V @ ImA           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         190pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         740mW (Ta)           Rds On (Max) @ Id, Vgs         30 Ohm @ 100mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-92-3           Package / Case         TO-226-3, TO-92-3 (TO-226AA)	Category	Discrete Semiconductor Products
Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         100mA (Tj)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         3.5V @ 1mA           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         190pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         740mW (Ta)           Rds On (Max) @ Id, Vgs         30 Ohm @ 100mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-92-3 (TO-226AA)		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 100mA (Tj) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 190pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 740mW (Ta) Rds On (Max) @ Id, Vgs 30 Ohm @ 100mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Package	TO-226-3, TO-92-3 (TO-226AA)
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  100mA (Tj)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  **ET Feature**  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Supplier Device Package  TO-92-3  Package / Case  **Cantinuous Drain (Id) @ 25°C  100mA (Tj)  **A.5V, 10V  3.5V @ 1mA  3.5V @ 1m	Series	-
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  100mA (Tj)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  3.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  30 Ohm @ 100mA, 10V  Operating Temperature  Supplier Device Package  TO-92-3  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C 100mA (Tj)  Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V  Vgs(th) (Max) @ Id 3.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 190pF @ 25V  Vgs (Max) ±20V  FET Feature - Power Dissipation (Max) 740mW (Ta)  Rds On (Max) @ Id, Vgs 30 Ohm @ 100mA, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-92-3  Package / Case TO-226-3, TO-92-3 (TO-226AA)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  3.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  30 Ohm @ 100mA, 10V  Operating Temperature  Supplier Device Package  Package / Case  TO-92-3  TO-92-3 (TO-226AA)	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  John Capacitance  Through Hole  Supplier Device Package  TO-92-3  TO-92-3 (TO-226AA)	Current - Continuous Drain (Id) @ 25°C	100mA (Tj)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  190pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  30 Ohm @ 100mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92-3  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds  190pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  30 Ohm @ 100mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92-3  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Vgs(th) (Max) @ Id	3.5V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)740mW (Ta)Rds On (Max) @ Id, Vgs30 Ohm @ 100mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - Power Dissipation (Max) 740mW (Ta) Rds On (Max) @ Id, Vgs 30 Ohm @ 100mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Input Capacitance (Ciss) (Max) @ Vds	190pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92-3  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs30 Ohm @ 100mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92-3  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Power Dissipation (Max)	740mW (Ta)
Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Rds On (Max) @ Id, Vgs	30 Ohm @ 100mA, 10V
Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-226-3, TO-92-3 (TO-226AA)	Mounting Type	Through Hole
	Supplier Device Package	TO-92-3
Report errors?	Package / Case	TO-226-3, TO-92-3 (TO-226AA)
		Report errors?

#### **VP2450N3-G Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **VP2450N3-G Payment Methods**



















## **VP2450N3-G Shipping Methods**













If you have any question about VP2450N3-G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com